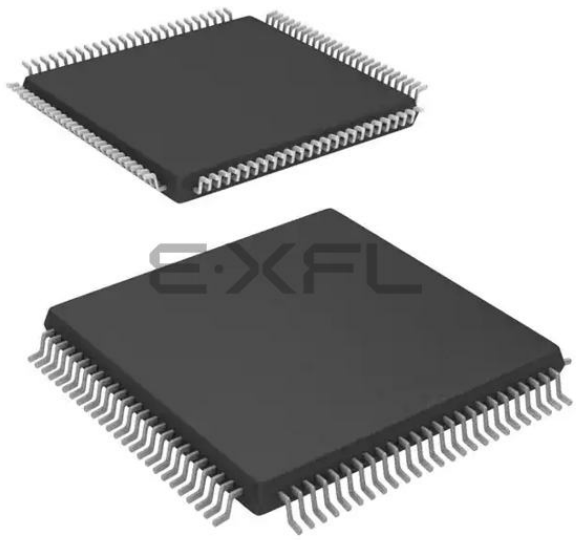
Microchip Technology - A3PN125-VQG100I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	71
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-vqg100i

2 – Low Power Modes in ProASIC3/E and ProASIC3 nano FPGAs

Introduction

The demand for low power systems and semiconductors, combined with the strong growth observed for value-based FPGAs, is driving growing demand for low power FPGAs. For portable and battery-operated applications, power consumption has always been the greatest challenge. The battery life of a system and on-board devices has a direct impact on the success of the product. As a result, FPGAs used in these applications should meet low power consumption requirements.

ProASIC®3/E and ProASIC3 nano FPGAs offer low power consumption capability inherited from their nonvolatile and live-at-power-up (LAPU) flash technology. This application note describes the power consumption and how to use different power saving modes to further reduce power consumption for power-conscious electronics design.

Power Consumption Overview

In evaluating the power consumption of FPGA technologies, it is important to consider it from a system point of view. Generally, the overall power consumption should be based on static, dynamic, inrush, and configuration power. Few FPGAs implement ways to reduce static power consumption utilizing sleep modes.

SRAM-based FPGAs use volatile memory for their configuration, so the device must be reconfigured after each power-up cycle. Moreover, during this initialization state, the logic could be in an indeterminate state, which might cause inrush current and power spikes. More complex power supplies are required to eliminate potential system power-up failures, resulting in higher costs. For portable electronics requiring frequent power-up and -down cycles, this directly affects battery life, requiring more frequent recharging or replacement.

$$\text{SRAM-Based FPGA Total Power Consumption} = P_{static} + P_{dynamic} + P_{inrush} + P_{config} \quad \textit{EQ 1}$$

$$\text{ProASIC3/E Total Power Consumption} = P_{static} + P_{dynamic} \quad \textit{EQ 2}$$

Unlike SRAM-based FPGAs, Microsemi flash-based FPGAs are nonvolatile and do not require power-up configuration. Additionally, Microsemi nonvolatile flash FPGAs are live at power-up and do not require additional support components. Total power consumption is reduced as the inrush current and configuration power components are eliminated.

Note that the static power component can be reduced in flash FPGAs (such as the ProASIC3/E devices) by entering User Low Static mode or Sleep mode. This leads to an extremely low static power component contribution to the total system power consumption.

The following sections describe the usage of Static (Idle) mode to reduce the power component, User Low Static mode to reduce the static power component, and Sleep mode and Shutdown mode to achieve a range of power consumption when the FPGA or system is idle. Table 2-1 on page 22 summarizes the different low power modes offered by ProASIC3/E devices.

Clock Aggregation Architecture

This clock aggregation feature allows a balanced clock tree, which improves clock skew. The physical regions for clock aggregation are defined from left to right and shift by one spine. For chip global networks, there are three types of clock aggregation available, as shown in Figure 3-10:

- Long lines that can drive up to four adjacent spines (A)
- Long lines that can drive up to two adjacent spines (B)
- Long lines that can drive one spine (C)

There are three types of clock aggregation available for the quadrant spines, as shown in Figure 3-10:

- I/Os or local resources that can drive up to four adjacent spines
- I/Os or local resources that can drive up to two adjacent spines
- I/Os or local resources that can drive one spine

As an example, A3PE600 and AFS600 devices have twelve spine locations: T1, T2, T3, T4, T5, T6, B1, B2, B3, B4, B5, and B6. Table 3-7 shows the clock aggregation you can have in A3PE600 and AFS600.

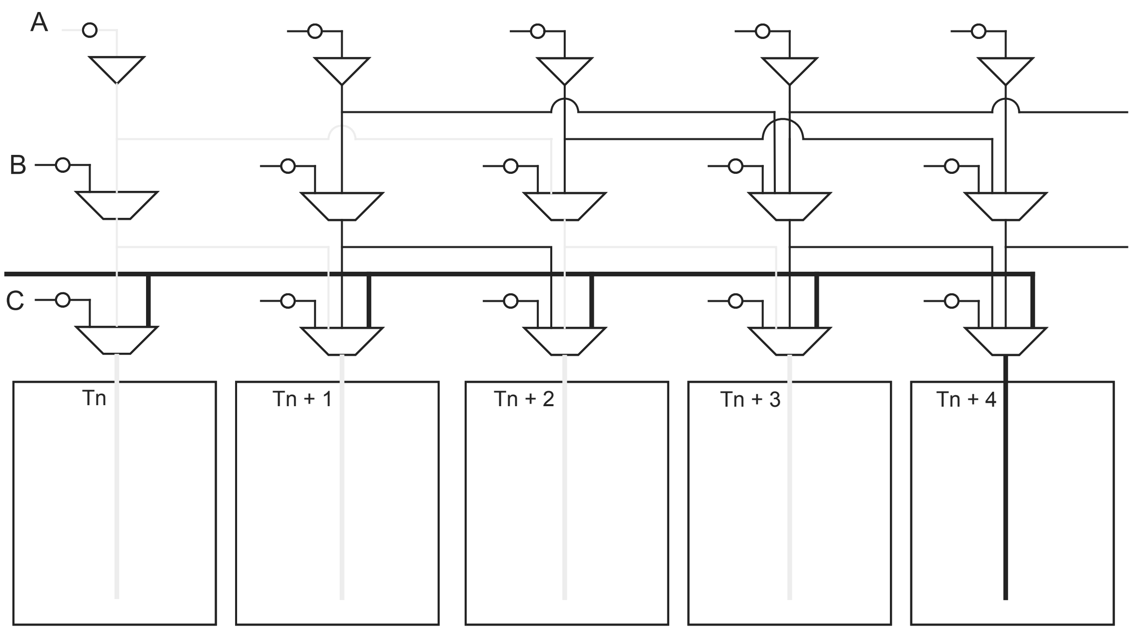

Figure 3-10 **• Four Spines Aggregation**

Table 3-7 **• Spine Aggregation in A3PE600 or AFS600**

Clock Aggregation	**Spine**
1 spine	T1, T2, T3, T4, T5, T6, B1, B2, B3, B4, B5, B6
2 spines	T1:T2, T2:T3, T3:T4, T4:T5, T5:T6, B1:B2, B2:B3, B3:B4, B4:B5, B5:B6
4 spines	B1:B4, B2:B5, B3:B6, T1:T4, T2:T5, T3:T6

The clock aggregation for the quadrant spines can cross over from the left to right quadrant, but not from top to bottom. The quadrant spine assignment T1:T4 is legal, but the quadrant spine assignment T1:B1 is not legal. Note that this clock aggregation is hardwired. You can always assign signals to spine T1 and B2 by instantiating a buffer, but this may add skew in the signal.

standard for CLKBUF is LVTTL in the current Microsemi Libero® System-on-Chip (SoC) and Designer software.

Table 3-9 **• I/O Standards within CLKBUF**

Name	Description
CLKBUF_LVCMOS5	LVCMOS clock buffer with 5.0 V CMOS voltage level
CLKBUF_LVCMOS33	LVCMOS clock buffer with 3.3 V CMOS voltage level
CLKBUF_LVCMOS25	LVCMOS clock buffer with 2.5 V CMOS voltage level[1]
CLKBUF_LVCMOS18	LVCMOS clock buffer with 1.8 V CMOS voltage level
CLKBUF_LVCMOS15	LVCMOS clock buffer with 1.5 V CMOS voltage level
CLKBUF_LVCMOS12	LVCMOS clock buffer with 1.2 V CMOS voltage level
CLKBUF_PCI	PCI clock buffer
CLKBUF_PCIX	PCIX clock buffer
CLKBUF_GTL25	GTL clock buffer with 2.5 V CMOS voltage level[1]
CLKBUF_GTL33	GTL clock buffer with 3.3 V CMOS voltage level[1]
CLKBUF_GTLP25	GTL+ clock buffer with 2.5 V CMOS voltage level[1]
CLKBUF_GTLP33	GTL+ clock buffer with 3.3 V CMOS voltage level[1]
CLKBUF_ HSTL _I	HSTL Class I clock buffer[1]
CLKBUF_ HSTL _II	HSTL Class II clock buffer[1]
CLKBUF_SSTL2_I	SSTL2 Class I clock buffer[1]
CLKBUF_SSTL2_II	SSTL2 Class II clock buffer[1]
CLKBUF_SSTL3_I	SSTL3 Class I clock buffer[1]
CLKBUF_SSTL3_II	SSTL3 Class II clock buffer[1]

Notes:

1. *Supported in only the IGLOOe, ProASIC3E, AFS600, and AFS1500 devices*
2. *By default, the CLKBUF macro uses the 3.3 V LVTTL I/O technology.*

The current synthesis tool libraries only infer the CLKBUF or CLKINT macros in the netlist. All other global macros must be instantiated manually into your HDL code. The following is an example of CLKBUF_LVCMOS25 global macro instantiations that you can copy and paste into your code:

VHDL

```
component clkbuf_lvcmos25
  port (pad : in std_logic; y : out std_logic);
end component

begin
-- concurrent statements
u2 : clkbuf_lvcmos25 port map (pad =>  ext_clk, y => int_clk);
end
```

Verilog

```
module design (______);

input _____;
output ______;

clkbuf_lvcmos25 u2 (.y(int_clk), .pad(ext_clk);

endmodule
```

IGLOO and ProASIC3 CCC Locations

In all IGLOO and ProASIC3 devices (except 10 k through 30 k gate devices, which do not contain PLLs), six CCCs are located in the same positions as the IGLOOe and ProASIC3E CCCs. Only one of the CCCs has an integrated PLL and is located in the middle of the west (middle left) side of the device. The other five CCCs are simplified CCCs and are located in the four corners and the middle of the east side of the device (Figure 4-14).

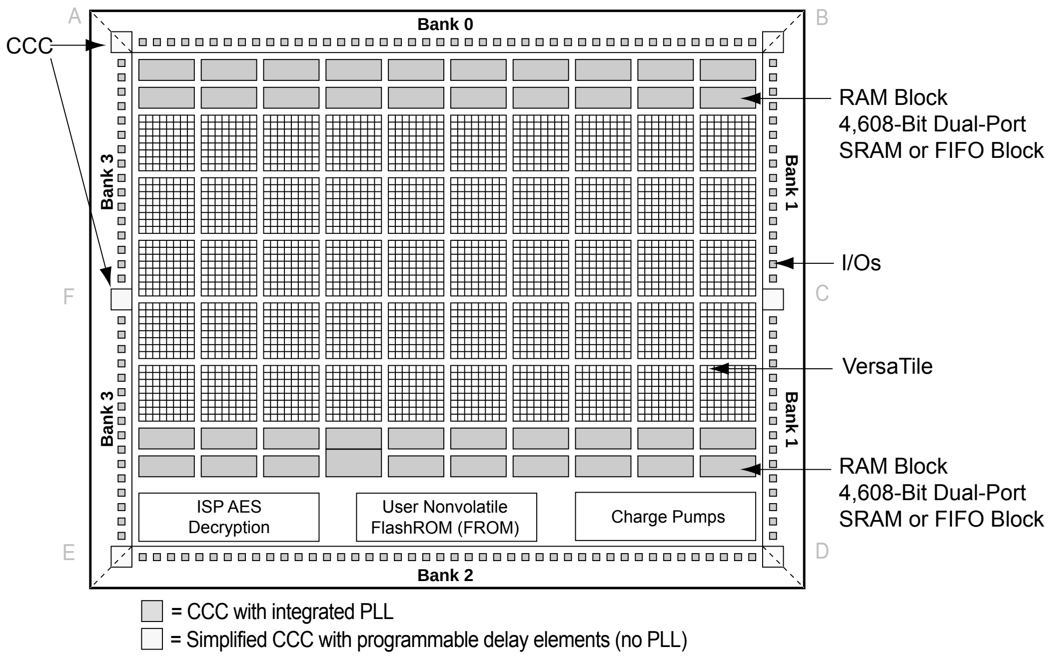

Figure 4-14 **• CCC Locations in IGLOO and ProASIC3 Family Devices (except 10 k through 30 k gate devices)**

Note: The number and architecture of the banks are different for some devices.

10 k through 30 k gate devices do not support PLL features. In these devices, there are two CCC-GLs at the lower corners (one at the lower right, and one at the lower left). These CCC-GLs do not have programmable delays.

Table 4-8 **• Configuration Bit Descriptions for the CCC Blocks (continued)**

Config. Bits	Signal	Name	Description
<31:29>	OAMUX[2:0]	GLA Output Select	Selects from the VCO's four phase outputs for GLA.
<28:24>	OCDIV[4:0]	Secondary 2 Output Divider	Sets the divider value for the GLC/YC outputs. Also known as divider *w* in Figure 4-20 on page 85. The divider value will be OCDIV[4:0] + 1.
<23:19>	OBDIV[4:0]	Secondary 1 Output Divider	Sets the divider value for the GLB/YB outputs. Also known as divider *v* in Figure 4-20 on page 85. The divider value will be OBDIV[4:0] + 1.
<18:14>	OADIV[4:0]	Primary Output Divider	Sets the divider value for the GLA output. Also known as divider *u* in Figure 4-20 on page 85. The divider value will be OADIV[4:0] + 1.
<13:7>	FBDIV[6:0]	Feedback Divider	Sets the divider value for the PLL core feedback. Also known as divider *m* in Figure 4-20 on page 85. The divider value will be FBDIV[6:0] + 1.
<6:0>	FINDIV[6:0]	Input Divider	Input Clock Divider (/n). Sets the divider value for the input delay on CLKA. The divider value will be FINDIV[6:0] + 1.

Notes:

1. *The <88:81> configuration bits are only for the Fusion dynamic CCC.*
2. *This value depends on the input clock source, so Layout must complete before these bits can be set. After completing Layout in Designer, generate the "CCC_Configuration" report by choosing* ***Tools*** *>* ***Report*** *>* ***CCC_Configuration****. The report contains the appropriate settings for these bits.*

- Use quadrant global region assignments by finding the clock net associated with the CCC macro under the Nets tab and creating a quadrant global region for the net, as shown in Figure 4-33.

Figure 4-33 **• Quadrant Clock Assignment for a Global Net**

External I/O–Driven CCCs

The above-mentioned recommendation for proper layout techniques will ensure the correct assignment. It is possible that, especially with External I/O–Driven CCC macros, placement of the CCC macro in a desired location may not be achieved. For example, assigning an input port of an External I/O–Driven CCC near a particular CCC location does not guarantee global assignments to the desired location. This is because the clock inputs of External I/O–Driven CCCs can be assigned to any I/O location; therefore, it is possible that the CCC connected to the clock input will be routed to a location other than the one closest to the I/O location, depending on resource availability and placement constraints.

Clock Placer

The clock placer is a placement engine for low power flash devices that places global signals on the chip global and quadrant global networks. Based on the clock assignment constraints for the chip global and quadrant global clocks, it will try to satisfy all constraints, as well as creating quadrant clock regions when necessary. If the clock placer fails to create the quadrant clock regions for the global signals, it will report an error and stop Layout.

The user must ensure that the constraints set to promote clock signals to quadrant global networks are valid.

Cascading CCCs

The CCCs in low power flash devices can be cascaded. Cascading CCCs can help achieve more accurate PLL output frequency results than those achievable with a single CCC. In addition, this technique is useful when the user application requires the output clock of the PLL to be a multiple of the reference clock by an integer greater than the maximum feedback divider value of the PLL (divide by 128) to achieve the desired frequency.

For example, the user application may require a 280 MHz output clock using a 2 MHz input reference clock, as shown in Figure 4-34 on page 110.

Figure 4-34 • **Cascade PLL Configuration**

Using internal feedback, we know from EQ 4-1 on page 86 that the maximum achievable output frequency from the primary output is

$$f_{GLA} = f_{CLKA} \times m / (n \times u) = 2 \text{ MHz} \times 128 / (1 \times 1) = 256 \text{ MHz}$$

EQ 4-5

Figure 4-35 shows the settings of the initial PLL. When configuring the initial PLL, specify the input to be either Hardwired I/O–Driven or External I/O–Driven. This generates a netlist with the initial PLL routed from an I/O. Do not specify the input to be Core Logic–Driven, as this prohibits the connection from the I/O pin to the input of the PLL.

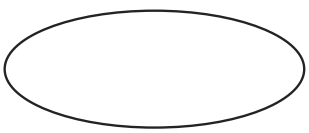

Figure 4-35 • **First-Stage PLL Showing Input of 2 MHz and Output of 256 MHz**

A second PLL can be connected serially to achieve the required frequency. EQ 4-1 on page 86 to EQ 4-3 on page 86 are extended as follows:

$$f_{GLA2} = f_{GLA} \times m_2 / (n_2 \times u_2) = f_{CLKA1} \times m_1 \times m_2 / (n_1 \times u_1 \times n_2 \times u_2) \text{ – Primary PLL Output Clock}$$

EQ 4-6

$$f_{GLB2} = f_{YB2} = f_{CLKA1} \times m_1 \times m_2 / (n_1 \times n_2 \times v_1 \times v_2) \text{ – Secondary 1 PLL Output Clock(s)}$$

EQ 4-7

$$f_{GLC2} = f_{YC2} = f_{CLKA1} \times m_1 \times m_2 / (n_1 \times n_2 \times w_1 \times w2) \text{ – Secondary 2 PLL Output Clock(s)}$$

EQ 4-8

In the example, the final output frequency (f_{output}) from the primary output of the second PLL will be as follows (EQ 4-9):

$$f_{output} = f_{GLA2} = f_{GLA} \times m_2 / (n_2 \times u_2) = 256 \text{ MHz} \times 70 / (64 \times 1) = 280 \text{ MHz}$$

EQ 4-9

Figure 4-36 on page 111 shows the settings of the second PLL. When configuring the second PLL (or any subsequent-stage PLLs), specify the input to be Core Logic–Driven. This generates a netlist with the second PLL routed internally from the core. Do not specify the input to be Hardwired I/O–Driven or External I/O–Driven, as these options prohibit the connection from the output of the first PLL to the input of the second PLL.

DEVICE_INFO displays the FlashROM content, serial number, Design Name, and checksum, as shown below:

```
EXPORT IDCODE[32] = 123261CF
EXPORT SILSIG[32] = 00000000
User information :
CHECKSUM: 61A0
Design Name:        TOP
Programming Method: STAPL
Algorithm Version: 1
Programmer: UNKNOWN
=========================================
FlashROM Information :
EXPORT Region_7_0[128] = FFFFFFFFFFFFFFFFFFFFFFFFFFFFFFFF
=========================================
Security Setting :
Encrypted FlashROM Programming Enabled.
Encrypted FPGA Array Programming Enabled.
=========================================
```

The Libero SoC file manager recognizes the UFC and MEM files and displays them in the appropriate view. Libero SoC also recognizes the multiple programming files if you choose the option to generate multiple files for multiple FlashROM contents in Designer. These features enable a user-friendly flow for the FlashROM generation and programming in Libero SoC.

Custom Serialization Using FlashROM

You can use FlashROM for device serialization or inventory control by using the Auto Inc region or Read From File region. FlashPoint will automatically generate the serial number sequence for the Auto Inc region with the **Start Value**, **Max Value**, and **Step Value** provided. If you have a unique serial number generation scheme that you prefer, the Read From File region allows you to import the file with your serial number scheme programmed into the region. See the *FlashPro User's Guide* for custom serialization file format information.

The following steps describe how to perform device serialization or inventory control using FlashROM:

1. Generate FlashROM using SmartGen. From the Properties section in the FlashROM Settings dialog box, select the **Auto Inc** or **Read From File** region. For the Auto Inc region, specify the desired step value. You will not be able to modify this value in the FlashPoint software.
2. Go through the regular design flow and finish place-and-route.
3. Select **Programming File in Designer** and open **Generate Programming File** (Figure 5-12 on page 128).
4. Click **Program FlashROM**, browse to the UFC file, and click **Next**. The FlashROM Settings window appears, as shown in Figure 5-13 on page 128.
5. Select the FlashROM page you want to program and the data value for the configured regions. The STAPL file generated will contain only the data that targets the selected FlashROM page.
6. Modify properties for the serialization.
   – For the Auto Inc region, specify the **Start** and **Max** values.
   – For the Read From File region, select the file name of the custom serialization file.
7. Select the FlashROM programming file type you want to generate from the two options below:
   – Single programming file for all devices: generates one programming file with all FlashROM values.
   – One programming file per device: generates a separate programming file for each FlashROM value.
8. Enter the number of devices you want to program and generate the required programming file.
9. Open the programming software and load the programming file. The programming software, FlashPro3 and Silicon Sculptor II, supports the device serialization feature. If, for some reason, the device fails to program a part during serialization, the software allows you to reuse or skip the serial data. Refer to the *FlashPro User's Guide* for details.

Refer to Table 7-10 on page 169 for more information about the slew rate and drive strength specification for LVTTL/LVCMOS 3.3 V, LVCMOS 2.5 V, LVCMOS 1.8 V, LVCMOS 1.5 V, and LVCMOS 1.2 V output buffers.

Table 7-14 **• nano Output Drive and Slew**

I/O Standards	2 mA	4 mA	6 mA	8 mA	Slew	
LVTTL / LVCMOS 3.3 V	✓	✓	✓	✓	High	Low
LVCMOS 2.5 V	✓	✓	✓	✓	High	Low
LVCMOS 1.8 V	✓	✓	–	–	High	Low
LVCMOS 1.5 V	✓	–	–	–	High	Low
LVCMOS 1.2 V	✓	–	–	–	High	Low

Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout

Each I/O voltage bank has a separate ground and power plane for input and output circuits. This isolation is necessary to minimize simultaneous switching noise from the input and output (SSI and SSO). The switching noise (ground bounce and power bounce) is generated by the output buffers and transferred into input buffer circuits, and vice versa.

SSOs can cause signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities (EQ 1 and EQ 2).

$$\text{Ground bounce noise voltage} = L(GND) \times di/dt \tag{EQ 1}$$

$$\text{VCCI dip noise voltage} = L(VCCI) \times di/dt \tag{EQ 2}$$

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to the SSO bus are LVTTL/LVCMOS inputs or LVTTL/LVCMOS outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to be considered are as follows:

- Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

For extensive data per package on the SSO and PCB issues, refer to the "ProASIC3/E SSO and Pin Placement and Guidelines" chapter of the *ProASIC3 Device Family User’s Guide*.

User I/O Naming Convention

Due to the comprehensive and flexible nature of nano Standard I/Os, a naming scheme is used to show the details of each I/O (Figure 7-8). The name identifies to which I/O bank it belongs.

I/O Nomenclature = FF/Gmn/IOuxwBy

Gmn is only used for I/Os that also have CCC access—i.e., global pins.

FF = Indicates the I/O dedicated for the Flash*Freeze mode activation pin

G = Global

m = Global pin location associated with each CCC on the device: A (northwest corner), B (northeast corner), C (east middle), D (southeast corner), E (southwest corner), and F (west middle)

n = Global input MUX and pin number of the associated Global location m—either A0, A1, A2, B0, B1, B2, C0, C1, or C2. Refer to the "Global Resources in Low Power Flash Devices" section on page 31 for information about the three input pins per clock source MUX at CCC location m.

u = I/O pair number in the bank, starting at 00 from the northwest I/O bank and proceeding in a clockwise direction

x = R (Regular—single-ended) for the I/Os that support single-ended standards.

w = S (Single-Ended)

B = Bank

y = Bank number (0–3). The Bank number starts at 0 from the northwest I/O bank and proceeds in a clockwise direction.

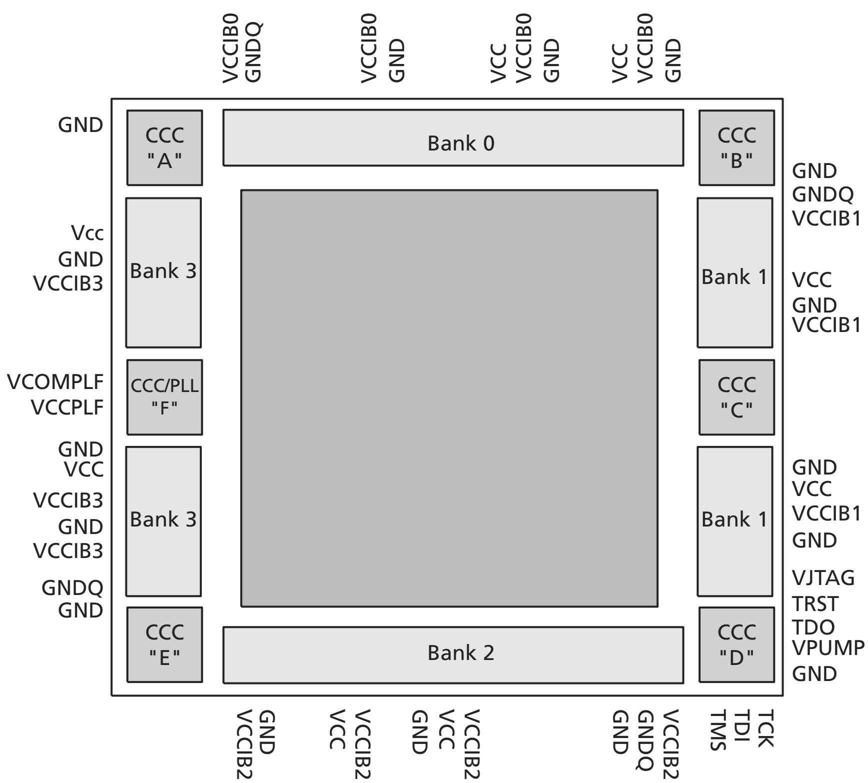

***Figure 7-8* • I/O Naming Conventions for nano Devices – Top View**

I/O Bank Architecture and CCC Naming Conventions

The nano products feature varying bank architectures which have been optimized to balance silicon area with I/O and clocking flexibility. The A standard naming scheme is used to illustrate the I/O Bank architecture and the CCCs associated with each architecture.

Table 7-16 **• A Standard Naming Scheme**

Name	Description
Bank x	Refers to the specific bank number within which an I/O resides
CCC	Clock Condition Circuit with simple clock delay operations as well as clock spine access
CCC-GL	Clock Condition Circuit with Global Locations for chip reach clocking. These CCCs support programmable delays but do not have an integrated PLL.
CCC-PLL	Clock Condition Circuit with integrated PLL and programmable delays
Chip Reach	Access to chip global lines
Quadrant Reach	Access to quadrant global lines

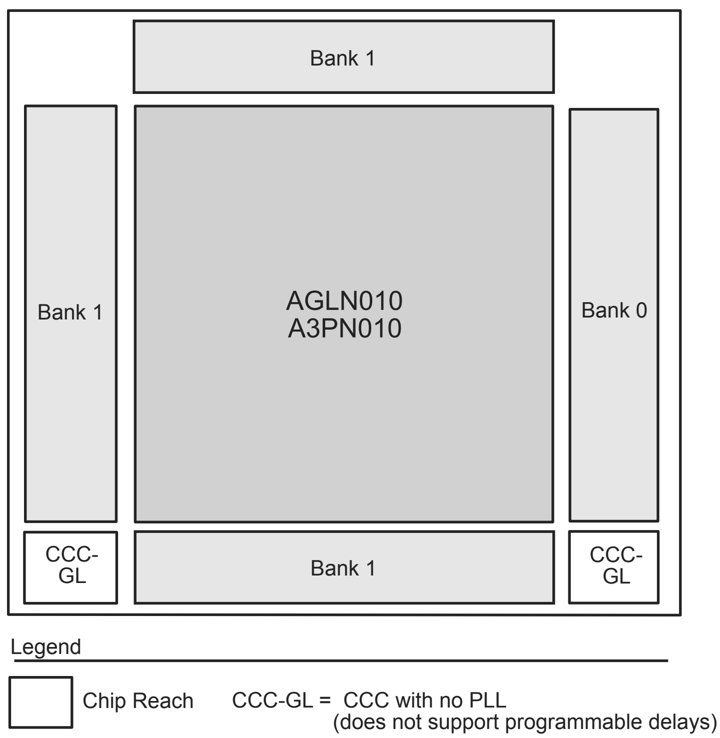

Figure 7-9 **• I/O Bank Architecture of AGLN010 and A3PN010 Devices**

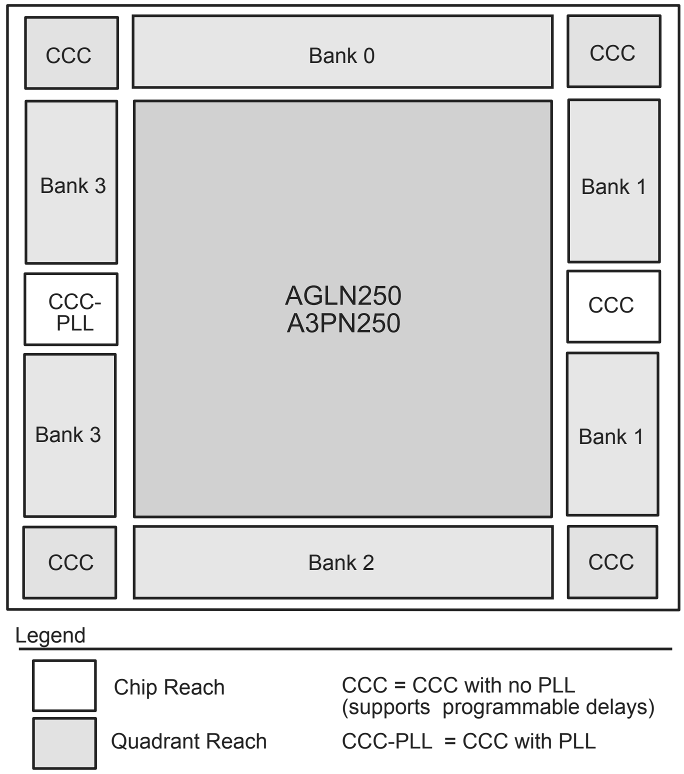

Figure 7-12 **• I/O Bank Architecture of AGLN250/A3PN250 Devices**

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions and Packaging" chapter of the appropriate device datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

I/O Bank Resource Usage

This is an important portion of the report. The user must meet the requirements stated in this table. Figure 8-10 shows the I/O Bank Resource Usage table included in the I/O bank report:

Figure 8-10 **• I/O Bank Resource Usage Table**

The example in Figure 8-10 shows that none of the I/O macros is assigned to the bank because more than one VCCI is detected.

I/O Voltage Usage

The I/O Voltage Usage table provides the number of VREF (E devices only) and V_{CCI} assignments required in the design. If the user decides to make I/O assignments manually (PDC or MVN), the issues listed in this table must be resolved before proceeding to Layout. As stated earlier, VREF assignments must be made if there are any voltage-referenced I/Os.

Figure 8-11 shows the I/O Voltage Usage table included in the I/O bank report.

Figure 8-11 **• I/O Voltage Usage Table**

The table in Figure 8-11 indicates that there are two voltage-referenced I/Os used in the design. Even though both of the voltage-referenced I/O technologies have the same VCCI voltage, their VREF voltages are different. As a result, two I/O banks are needed to assign the VCCI and VREF voltages.

In addition, there are six single-ended I/Os used that have the **same VCCI voltage. Since two banks are already assigned with the same VCCI voltage and there are enough u**nused bonded I/Os in

DDR Input Register

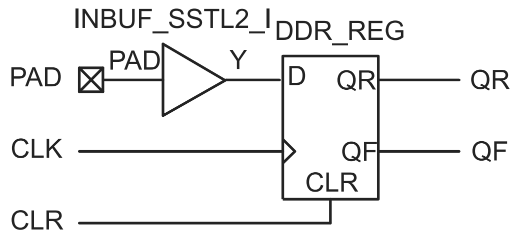

Figure 9-5 **• DDR Input Register (SSTL2 Class I)**

The corresponding structural representations, as generated by SmartGen, are shown below:

Verilog

```
module DDR_InBuf_SSTL2_I(PAD,CLR,CLK,QR,QF);

input   PAD, CLR, CLK;
output  QR, QF;

wire Y;

  INBUF_SSTL2_I INBUF_SSTL2_I_0_inst(.PAD(PAD),.Y(Y));
  DDR_REG DDR_REG_0_inst(.D(Y),.CLK(CLK),.CLR(CLR),.QR(QR),.QF(QF));

endmodule
```

VHDL

```
library ieee;
use ieee.std_logic_1164.all;
--The correct library will be inserted automatically by SmartGen
library proasic3; use proasic3.all;
--library fusion; use fusion.all;
--library igloo; use igloo.all;

entity DDR_InBuf_SSTL2_I is
  port(PAD, CLR, CLK : in std_logic;  QR, QF : out std_logic) ;
end DDR_InBuf_SSTL2_I;

architecture DEF_ARCH of  DDR_InBuf_SSTL2_I is

  component INBUF_SSTL2_I
    port(PAD : in std_logic := 'U'; Y : out std_logic) ;
  end component;

  component DDR_REG
    port(D, CLK, CLR : in std_logic := 'U'; QR, QF : out std_logic) ;
  end component;

signal Y : std_logic ;

begin

  INBUF_SSTL2_I_0_inst : INBUF_SSTL2_I
  port map(PAD => PAD, Y => Y);
  DDR_REG_0_inst : DDR_REG
  port map(D => Y, CLK => CLK, CLR => CLR, QR => QR, QF => QF);

end DEF_ARCH;
```

Related Documents

Below is a list of related documents, their location on the Microsemi SoC Products Group website, and a brief summary of each document.

Application Notes

Programming Antifuse Devices

http://www.microsemi.com/soc/documents/AntifuseProgram_AN.pdf

Implementation of Security in Actel's ProASIC and ProASIC^PLUS Flash-Based FPGAs

http://www.microsemi.com/soc/documents/Flash_Security_AN.pdf

User's Guides

FlashPro Programmers

FlashPro4,[1] FlashPro3, FlashPro Lite, and FlashPro[2]

http://www.microsemi.com/soc/products/hardware/program_debug/flashpro/default.aspx

FlashPro User's Guide

http://www.microsemi.com/soc/documents/FlashPro_UG.pdf

The FlashPro User's Guide includes hardware and software setup, self-test instructions, use instructions, and a troubleshooting / error message guide.

Silicon Sculptor 3 and Silicon Sculptor II

http://www.microsemi.com/soc/products/hardware/program_debug/ss/default.aspx

Other Documents

http://www.microsemi.com/soc/products/solutions/security/default.aspx#flashlock

The security resource center describes security in Microsemi Flash FPGAs.

Quality and Reliability Guide

http://www.microsemi.com/soc/documents/RelGuide.pdf

Programming and Functional Failure Guidelines

http://www.microsemi.com/soc/documents/FA_Policies_Guidelines_5-06-00002.pdf

1. *FlashPro4 replaced FlashPro3 in Q1 2010.*
2. *FlashPro is no longer available.*

3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.

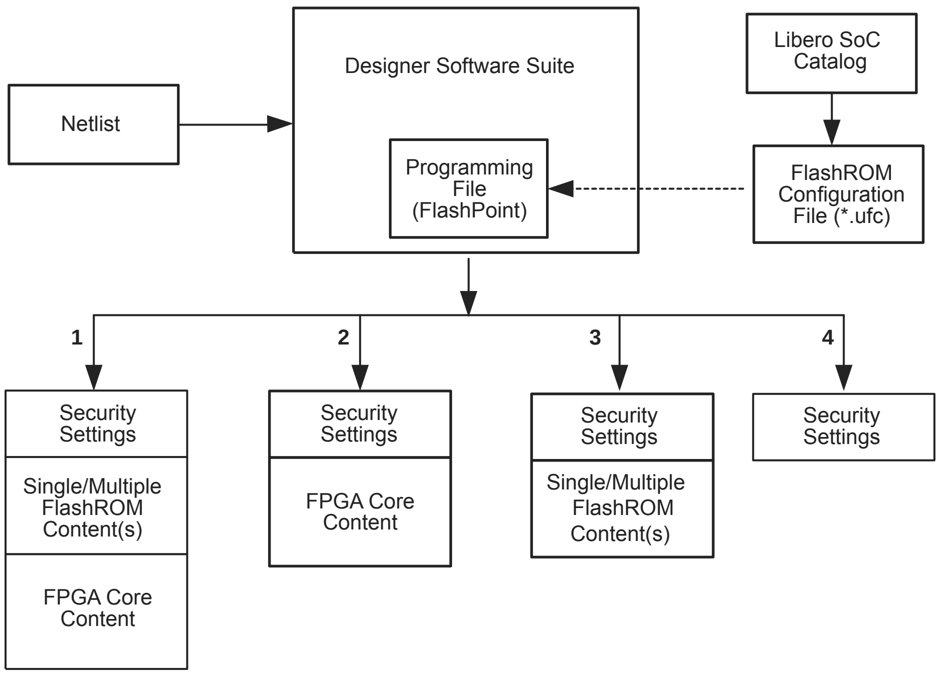

Figure 12-4 **• Flexible Programming File Generation for Different Applications**

Programming Solution

For device programming, any IEEE 1532–compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock – TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file – STAPL
- Daisy chain – Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming – Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply – The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

SRAM Initialization

Users can also initialize embedded SRAMs of the low power flash devices. The initialization of the embedded SRAM blocks of the design can be done using UJTAG tiles, where the initialization data is imported using the TAP Controller. Similar functionality is available in ProASICPLUS devices using JTAG. The guidelines for implementation and design examples are given in the *RAM Initialization and ROM Emulation in ProASICPLUS Devices* application note.

SRAMs are volatile by nature; data is lost in the absence of power. Therefore, the initialization process should be done at each power-up if necessary.

FlashROM Read-Back Using JTAG

The low power flash architecture contains a dedicated nonvolatile FlashROM block, which is formatted into eight 128-bit pages. For more information on FlashROM, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 117. The contents of FlashROM are available to the VersaTiles during normal operation through a read operation. As a result, the UJTAG macro can be used to provide the FlashROM contents to the JTAG port during normal operation. Figure 16-7 illustrates a simple block diagram of using UJTAG to read the contents of FlashROM during normal operation.

The FlashROM read address can be provided from outside the FPGA through the TDI input or can be generated internally using the core logic. In either case, data serialization logic is required (Figure 16-7) and should be designed using the VersaTile core logic. FlashROM contents are read asynchronously in parallel from the flash memory and shifted out in a synchronous serial format to TDO. Shifting the serial data out of the serialization block should be performed while the TAP is in UDRSH mode. The coordination between TCK and the data shift procedure can be done using the TAP state machine by monitoring UDRSH, UDRCAP, and UDRUPD.

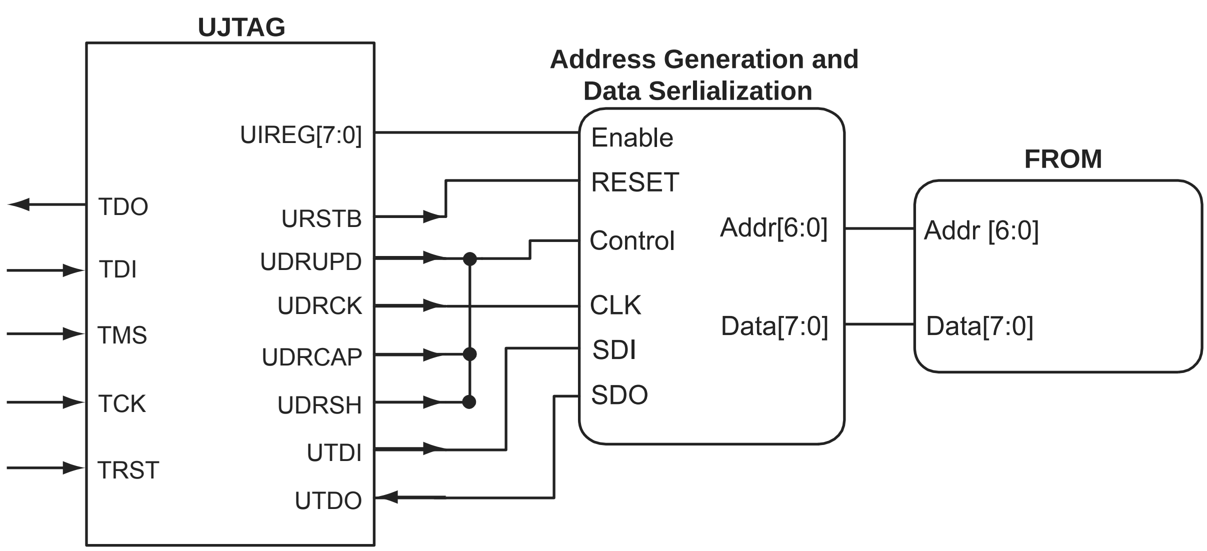

***Figure 16-7* • Block Diagram of Using UJTAG to Read FlashROM Contents**

17 – Power-Up/-Down Behavior of Low Power Flash Devices

Introduction

Microsemi's low power flash devices are flash-based FPGAs manufactured on a 0.13 µm process node. These devices offer a single-chip, reprogrammable solution and support Level 0 live at power-up (LAPU) due to their nonvolatile architecture.

Microsemi's low power flash FPGA families are optimized for logic area, I/O features, and performance. IGLOO® devices are optimized for power, making them the industry's lowest power programmable solution. IGLOO PLUS FPGAs offer enhanced I/O features beyond those of the IGLOO ultra-low power solution for I/O-intensive low power applications. IGLOO nano devices are the industry's lowest-power cost-effective solution. ProASIC3®L FPGAs balance low power with high performance. The ProASIC3 family is Microsemi's high-performance flash FPGA solution. ProASIC3 nano devices offer the lowest-cost solution with enhanced I/O capabilities.

Microsemi's low power flash devices exhibit very low transient current on each power supply during power-up. The peak value of the transient current depends on the device size, temperature, voltage levels, and power-up sequence.

The following devices can have inputs driven in while the device is not powered:

- IGLOO (AGL015 and AGL030)
- IGLOO nano (all devices)
- IGLOO PLUS (AGLP030, AGLP060, AGLP125)
- IGLOOe (AGLE600, AGLE3000)
- ProASIC3L (A3PE3000L)
- ProASIC3 (A3P015, A3P030)
- ProASIC3 nano (all devices)
- ProASIC3E (A3PE600, A3PE1500, A3PE3000)
- Military ProASIC3EL (A3PE600L, A3PE3000L, but not A3P1000)
- RT ProASIC3 (RT3PE600L, RT3PE3000L)

The driven I/Os do not pull up power planes, and the current draw is limited to very small leakage current, making them suitable for applications that require cold-sparing. These devices are hot-swappable, meaning they can be inserted in a live power system.[1]

1. *For more details on the levels of hot-swap compatibility in Microsemi's low power flash devices, refer to the "Hot-Swap Support" section in the I/O Structures chapter of the FPGA fabric user's guide for the device you are using.*

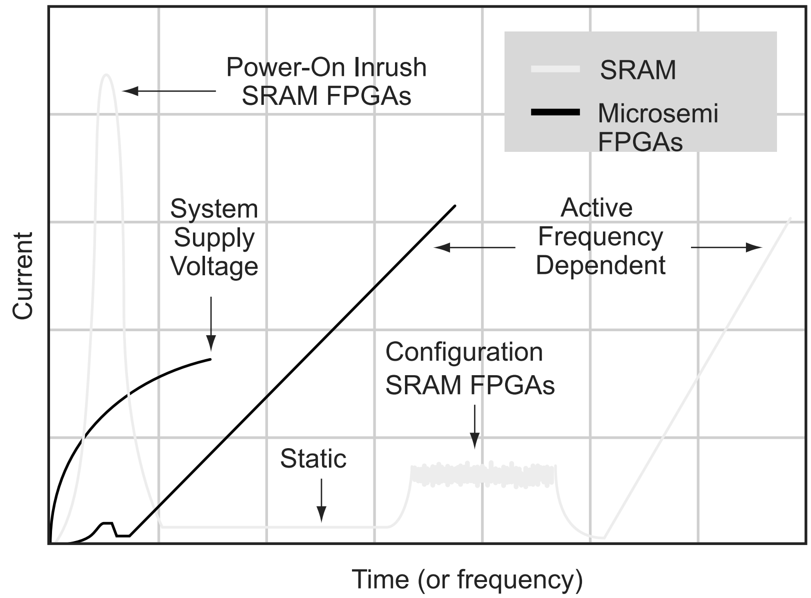

Figure 17-1 **• Types of Power Consumption in SRAM FPGAs and Microsemi Nonvolatile FPGAs**

Transient Current on VCC

The characterization of the transient current on VCC is performed on nearly all devices within the IGLOO, ProASIC3L, and ProASIC3 families. A sample size of five units is used from each device family member. All the device I/Os are internally pulled down while the transient current measurements are performed. For ProASIC3 devices, the measurements at typical conditions show that the maximum transient current on VCC, when the power supply is powered at ramp-rates ranging from 15 V/ms to 0.15 V/ms, does not exceed the maximum standby current specified in the device datasheets. Refer to the DC and Switching Characteristics chapters of the *ProASIC3 Flash Family FPGAS* datasheet and *ProASIC3E Flash Family FPGAs* datasheet for more information.

Similarly, IGLOO, IGLOO nano, IGLOO PLUS, and ProASIC3L devices exhibit very low transient current on VCC. The transient current does not exceed the typical operating current of the device while in active mode. For example, the characterization of AGL600-FG256 V2 and V5 devices has shown that the transient current on VCC is typically in the range of 1–5 mA.

Transient Current on VCCI

The characterization of the transient current on VCCI is performed on devices within the IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3, ProASIC3 nano, and ProASIC3L groups of devices, similarly to VCC transient current measurements. For ProASIC3 devices, the measurements at typical conditions show that the maximum transient current on VCCI, when the power supply is powered at ramp-rates ranging from 33 V/ms to 0.33 V/ms, does not exceed the maximum standby current specified in the device datasheet. Refer to the DC and Switching Characteristics chapters of the *ProASIC3 Flash Family FPGAS* datasheet and *ProASIC3E Flash Family FPGAs* datasheet for more information.

Similarly, IGLOO, IGLOO PLUS, and ProASIC3L devices exhibit very low transient current on VCCI. The transient current does not exceed the typical operating current of the device while in active mode. For example, the characterization of AGL600-FG256 V2 and V5 devices has shown that the transient current on VCCI is typically in the range of 1–2 mA.

Internal Pull-Up and Pull-Down

Low power flash device I/Os are equipped with internal weak pull-up/-down resistors that can be used by designers. If used, these internal pull-up/-down resistors will be activated during power-up, once both VCC and VCCI are above their functional activation level. Similarly, during power-down, these internal pull-up/-down resistors will turn off once the first supply voltage falls below its brownout deactivation level.

Cold-Sparing

In cold-sparing applications, voltage can be applied to device I/Os before and during power-up. Cold-sparing applications rely on three important characteristics of the device:

1. I/Os must be tristated before and during power-up.
2. Voltage applied to the I/Os must not power up any part of the device.
3. VCCI should not exceed 3.6 V, per datasheet specifications.

As described in the "Power-Up to Functional Time" section on page 312, Microsemi's low power flash I/Os are tristated before and during power-up until the last voltage supply (VCC or VCCI) is powered up past its functional level. Furthermore, applying voltage to the FPGA I/Os does not pull up VCC or VCCI and, therefore, does not partially power up the device. Table 17-4 includes the cold-sparing test results on A3PE600-PQ208 devices. In this test, leakage current on the device I/O and residual voltage on the power supply rails were measured while voltage was applied to the I/O before power-up.

***Table 17-4* • Cold-Sparing Test Results for A3PE600 Devices**

Device I/O	Residual Voltage (V)		Leakage Current
	VCC	VCCI	
Input	0	0.003	<1 µA
Output	0	0.003	<1 µA

VCCI must not exceed 3.6 V, as stated in the datasheet specification. Therefore, ProASIC3E devices meet all three requirements stated earlier in this section and are suitable for cold-sparing applications.

The following devices and families support cold-sparing:

- IGLOO: AGL015 and AGL030
- All IGLOO nano
- All IGLOO PLUS
- All IGLOOe
- ProASIC3L: A3PE3000L
- ProASIC3: A3P015 and A3P030
- All ProASIC3 nano
- All ProASIC3E
- Military ProASIC3EL: A3PE600L and A3PE3000L
- RT ProASIC3: RT3PE600L and RT3PE3000L